

# Lonten N-channel 20V, 4A, 42mΩ Power MOSFET

### **Description**

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

#### **Features**

- $20V,4A,R_{DS(ON).max}=42m\Omega@V_{GS}=4.5V$
- Improved dv/dt capability
- Fast switching
- Green device available

#### **Applications**

- Battery protection
- Load switch
- Power management

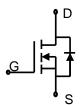
#### **Product Summary**

 $\begin{array}{ll} V_{DSS} & 20V \\ R_{DS(on).max}@~V_{GS}\!\!=\!\!4.5V & 42m\Omega \\ I_D & 4A \end{array}$ 

### **Pin Configuration**







N-Channel MOSFET



#### **Absolute Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{ t DSS}$	20	V
Continuous drain current ( T <sub>A</sub> = 25°C )		4	А
Continuous drain current ( T <sub>A</sub> = 100°C )	I <sub>D</sub>	2.5	А
Pulsed drain current <sup>1)</sup>	I <sub>DM</sub>	16	А
Gate-Source voltage	$V_{GSS}$	±12	V
Power Dissipation ( T <sub>A</sub> = 25°C )	P <sub>D</sub>	1	W
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C
Operating Junction Temperature Range	TJ	-55 to +150	°C

#### **Thermal Characteristics**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W



**Package Marking and Ordering Information** 

Device	Device Package	Marking
LNSC2302	SOT-23	2302

**Electrical Characteristics**  $T_J = 25^{\circ}\text{C}$  unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Static characteristics				•		
Drain-source breakdown voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0 V, I <sub>D</sub> =250uA	20			V
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.75	1.2	V
		V <sub>DS</sub> =20 V, V <sub>GS</sub> =0 V, T <sub>J</sub> = 25°C			1	μA
Drain-source leakage current	I <sub>DSS</sub>	V <sub>DS</sub> =16 V, V <sub>GS</sub> =0 V, T <sub>J</sub> = 125°C			10	μΑ
Gate leakage current, Forward	I <sub>GSSF</sub>	V <sub>GS</sub> =12 V, V <sub>DS</sub> =0 V			100	nA
Gate leakage current, Reverse	I <sub>GSSR</sub>	V <sub>GS</sub> =-12 V, V <sub>DS</sub> =0 V			-100	nA
Drain-source on-state resistance	D	V <sub>GS</sub> =4.5 V, I <sub>D</sub> =3 A		27	42	mΩ
Diam-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =2.5 V, I <sub>D</sub> =2.5 A		33	55	mΩ
Forward transconductance	<b>g</b> fs	$V_{DS} = 5 \text{ V}$ , $I_D = 3 \text{A}$		10		S
Dynamic characteristics						
Input capacitance	C <sub>iss</sub>			327		pF
Output capacitance	C <sub>oss</sub>	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$ $F = 1 \text{MHz}$		50		
Reverse transfer capacitance	C <sub>rss</sub>	- 1 = 11VII 12		42.8		
Turn-on delay time	t <sub>d(on)</sub>			7		
Rise time	t <sub>r</sub>	V <sub>DD</sub> = 10V,V <sub>GS</sub> =4.5V, I <sub>D</sub> =3 A		12		ne
Turn-off delay time	t <sub>d(off)</sub>	VDD = 10V,VGS=4.0V, ID =0 A		48		. ns
Fall time	t <sub>f</sub>			20		
Gate resistance	$R_g$	V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,f=1MHz		3.6		Ω
Gate charge characteristics						
Gate to source charge	$Q_{gs}$			8		
Gate to drain charge	$Q_{gd}$	$V_{DS}$ =10V, $I_{D}$ =3A, $V_{GS}$ = 4.5V		0.7		nC
Gate charge total	$Q_g$	V <sub>GS</sub> = 4.5V		3.2		
Drain-Source diode characteris	tics and Maxir	num Ratings				•
Continuous Source Current	Is				4	Α
Pulsed Source Current <sup>2)</sup>	I <sub>SM</sub>				16	Α
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =3A, T <sub>J</sub> =25℃			1.2	V

#### Notes:

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<sup>1:</sup> Repetitive Rating: Pulse width limited by maximum junction temperature.

<sup>2:</sup> Pulse Test: Pulse Width  $\leq 300 \, \mu \, s$ , Duty Cycle  $\leq 2\%$ .



### **Electrical Characteristics Diagrams**

Figure 1. Typ. Output Characteristics

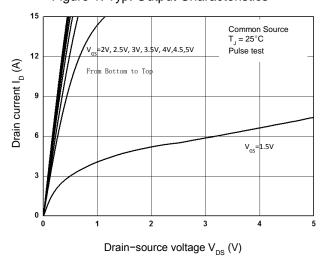


Figure 2. Transfer Characteristics

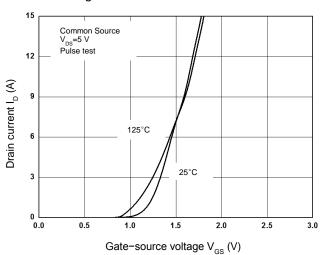


Figure 3. Capacitance Characteristics

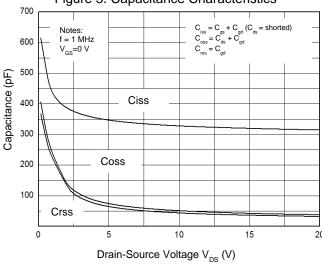


Figure 4. Gate Charge Waveform

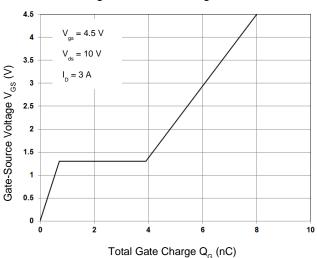


Figure 5. Body-Diode Characteristics

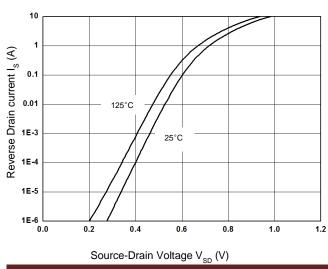


Figure 6. Rdson-Drain Current

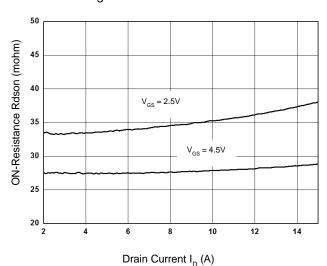




Figure 7. Rdson-Junction Temperature(°C)

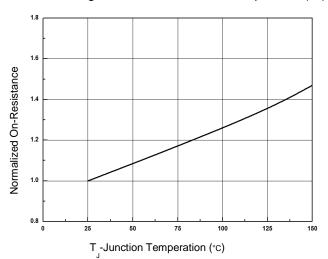


Figure 8. Maximum Safe Operating Area

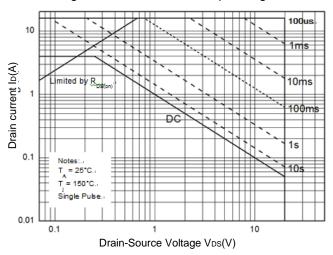
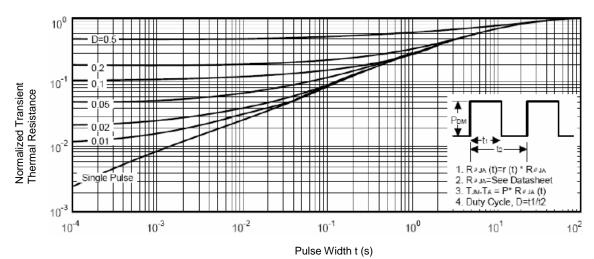


Figure 6. Normalized Maximum Transient Thermal Impedance (RthJA)

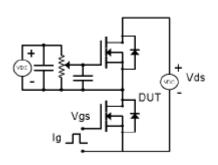


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### **Test Circuit & Waveform**

Figure 8. Gate Charge Test Circuit & Waveform



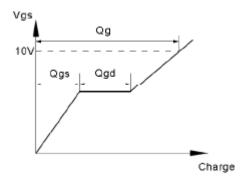
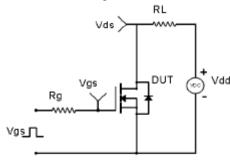


Figure 9. Resistive Switching Test Circuit & Waveforms



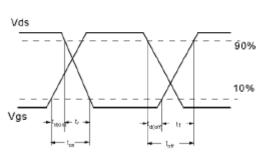
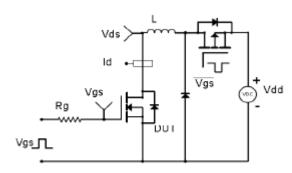


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



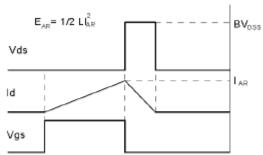
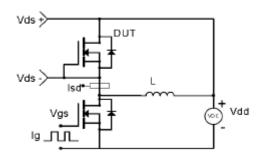
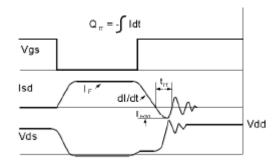


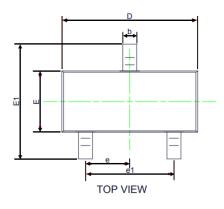
Figure 11. Diode Recovery Circuit & Waveform

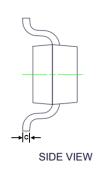




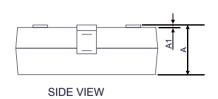


# **Mechanical Dimensions for SOT-23**

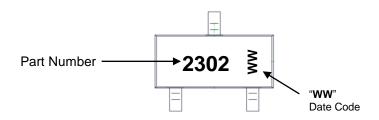




COMMON DIMENSIONS					
SYMBOL	MILLIMETERS		INCHS		
	MIN	MAX	MIN	MAX	
А	0.95	1.40	0.037	0.055	
A1	0.01	0.10	0.000	0.004	
b	0.35	0.50	0.014	0.020	
С	0.08	0.19	0.003	0.007	
D	2.70	3.10	0.106	0.122	
E	1.20	1.65	0.047	0.065	
E1	2.20	3.00	0.087	0.118	
е	0.95 TYP.		0.037	TYP.	
e1	1.78	2.04	0.070	0.080	



## **SOT-23 Part Marking Information**





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